MC74LCX86

Low-Voltage CMOS Quad 2-Input XOR Gate

With 5 V−Tolerant Inputs

The MC74LCX86 is a high performance, quad 2−input XOR gate operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows MC74LCX86 inputs to be safely driven from 5.0 V devices.

Current drive capability is 24 mA at the outputs.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.0 V Tolerant Inputs − Interface Capability With 5.0 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V
                         Machine Model >200 V
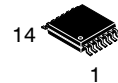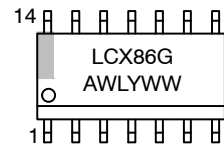- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant
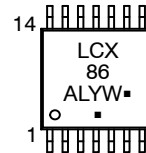
ON Semiconductor®

MARKING DIAGRAMS
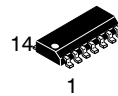
SOIC−14
D SUFFIX
CASE 751A

```
14
   LCX86G
   AWLYWW
1
```

TSSOP−14
DT SUFFIX
CASE 948G

```
14
   LCX
   86
   ALYW■
1
```

A	= Assembly Location
L, WL	= Wafer Lot
Y, YY	= Year
W, WW	= Work Week
G or ■	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.
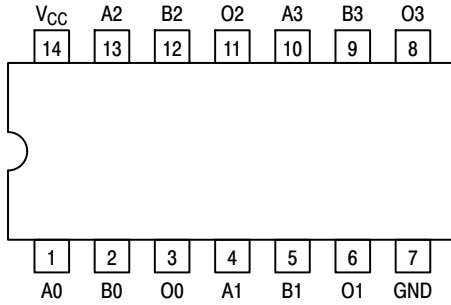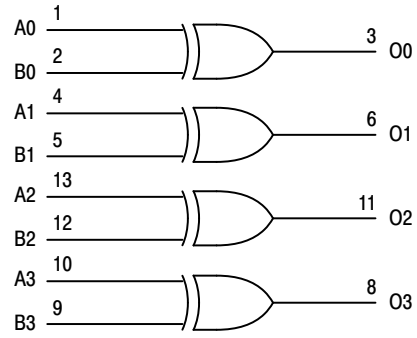
MC74LCX86

Figure 1. Pinout: 14−Lead (Top View)

Figure 2. Logic Diagram

PIN NAMES

Pins	Function
An, Bn	Data Inputs
On	Outputs

TRUTH TABLE

Inputs		Outputs
An	**Bn**	**On**
L	L	L
L	H	H
H	L	H
H	H	L

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V_{CC}	DC Supply Voltage	−0.5 to +7.0		V
V_I	DC Input Voltage	$-0.5 \leq V_I \leq +7.0$		V
V_O	DC Output Voltage	$-0.5 \leq V_O \leq V_{CC} + 0.5$	Note 1	V
I_{IK}	DC Input Diode Current	−50	$V_I <$ GND	mA
I_{OK}	DC Output Diode Current	−50	$V_O <$ GND	mA
		+50	$V_O > V_{CC}$	mA
I_O	DC Output Source/Sink Current	±50		mA
I_{CC}	DC Supply Current Per Supply Pin	±100		mA
I_{GND}	DC Ground Current Per Ground Pin	±100		mA
T_{STG}	Storage Temperature Range	−65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.
1. Output in HIGH or LOW State. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Units

V_{CC}	Supply Voltage
	    Operating
	    Data Retention Only
		
		2.0
		1.5
			
			3.3
			3.3
				
				3.6
				3.6
					V

V_I	Input Voltage	0		5.5	V
V_O	Output Voltage (HIGH or LOW State)	0		V_{CC}	V
I_{OH}	HIGH Level Output Current, V_{CC} = 3.0 V – 3.6 V			−24	mA
I_{OL}	LOW Level Output Current, V_{CC} = 3.0 V – 3.6 V			24	mA
I_{OH}	HIGH Level Output Current, V_{CC} = 2.7 V – 3.0 V			−12	mA
I_{OL}	LOW Level Output Current, V_{CC} = 2.7 V – 3.0 V			12	mA
T_A	Operating Free–Air Temperature	−40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = −40°C to +85°C		Units
			Min	Max	
V_{IH}	HIGH Level Input Voltage (Note 2)	2.7 V ≤ V_{CC} ≤ 3.6 V	2.0		V
V_{IL}	LOW Level Input Voltage (Note 2)	2.7 V ≤ V_{CC} ≤ 3.6 V		0.8	V
V_{OH}	HIGH Level Output Voltage	2.7 V ≤ V_{CC} ≤ 3.6 V; I_{OH} = −100 μA	V_{CC} − 0.2		V
		V_{CC} = 2.7 V; I_{OH} = −12 mA	2.2		
		V_{CC} = 3.0 V; I_{OH} = −18 mA	2.4		
		V_{CC} = 3.0 V; I_{OH} = −24 mA	2.2		
V_{OL}	LOW Level Output Voltage	2.7 V ≤ V_{CC} ≤ 3.6 V; I_{OL} = 100 μA		0.2	V
		V_{CC} = 2.7 V; I_{OL}= 12 mA		0.4	
		V_{CC} = 3.0 V; I_{OL} = 16 mA		0.4	
		V_{CC} = 3.0 V; I_{OL} = 24 mA		0.55	
I_{OFF}	Power Off Leakage Current	V_{CC} = 0, V_{IN} = 5.5 V or V_{OUT} = 5.5 V		10	μA
I_{IN}	Input Leakage Current	V_{CC} = 3.6 V, V_{IN} = 5.5 V or GND		±5	μA
I_{CC}	Quiescent Supply Current	V_{CC} = 3.6 V, V_{IN} = 5.5 V or GND		10	μA
ΔI_{CC}	Increase in I_{CC} per Input	2.3 ≤ V_{CC} ≤ 3.6 V; V_{IH} = V_{CC} − 0.6 V		500	μA

2. These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS (t_R = t_F = 2.5ns; C_L = 50pF; R_L = 500Ω)

Symbol	Parameter	Waveform	Limits			Units
			T_A = −40°C to +85°C			
			V_{CC} = 3.0 V to 3.6 V		V_{CC} = 2.7 V	
			Min	Max	Max	
t_{PLH} t_{PHL}	Propagation Delay Input to Output	1,2	1.5 1.5	6.5 6.5	7.0 7.0	ns
t_{OSHL} t_{OSLH}	Output–to–Output Skew (Note 3)			1.0 1.0		ns

3. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t_{OSHL}) or LOW–to–HIGH (t_{OSLH}); parameter guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = +25°C			Units
			Min	Typ	Max	
V_{OLP}	Dynamic LOW Peak Voltage (Note 4)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V		0.8		V
V_{OLV}	Dynamic LOW Valley Voltage (Note 4)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V		0.8		V

4. Number of outputs defined as "n". Measured with "n–1" outputs switching from HIGH–to–LOW or LOW–to–HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	7	pF
C_{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	25	pF

ORDERING INFORMATION

Device	Package	Shipping[†]
MC74LCX86DR2G	SOIC–14 (Pb–Free)	2500 Tape & Reel
MC74LCX86DTR2G	TSSOP–14 (Pb–Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
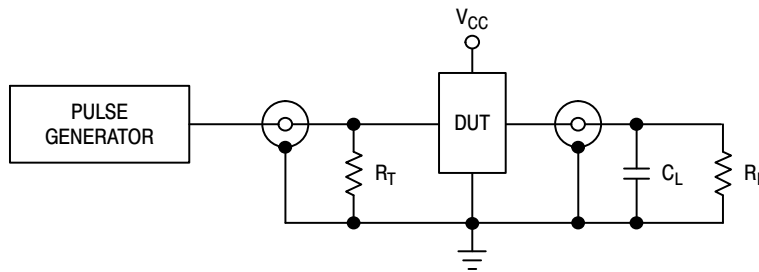
MC74LCX86
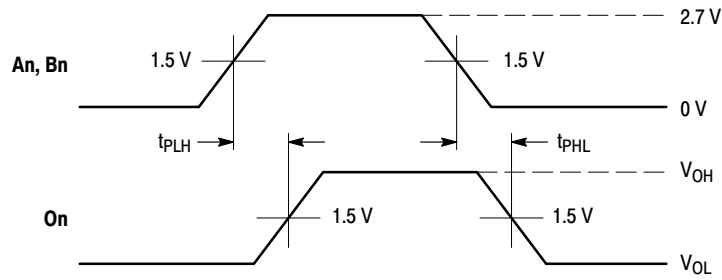
WAVEFORM 1 – NON–INVERTING PROPAGATION DELAYS
$t_R = t_F = 2.5$ ns, 10% to 90%; f = 1 MHz; $t_W = 500$ ns
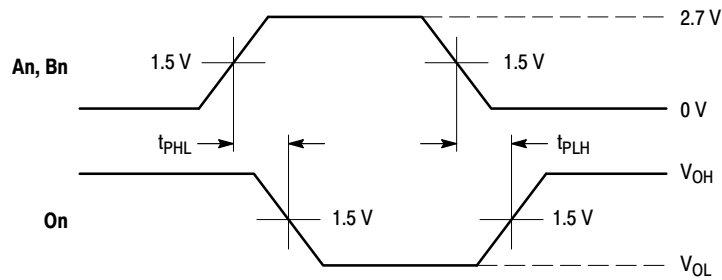
WAVEFORM 2 – INVERTING PROPAGATION DELAYS
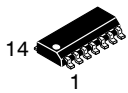$t_R = t_F = 2.5$ ns, 10% to 90%; f = 1 MHz; $t_W = 500$ ns

Figure 3. AC Waveforms

C_L = 50pF or equivalent (Includes jig and probe capacitance)
$R_L = R_1 = 500\ \Omega$ or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

SOIC−14 NB
CASE 751A−03
ISSUE L

SCALE 1:1

DATE 03 FEB 2016
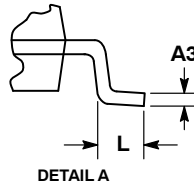
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DETAIL A

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

SEATING PLANE

SOLDERING FOOTPRINT*

6.50

14X 1.18

1.27 PITCH

14X 0.58

DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*

XXXXXXXXXG
AWLYWW

XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42565B	
DESCRIPTION:	SOIC−14 NB	PAGE 1 OF 2

STYLE 1:
PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. NO CONNECTION
 5. ANODE/CATHODE
 6. NO CONNECTION
 7. ANODE/CATHODE
 8. ANODE/CATHODE
 9. ANODE/CATHODE
 10. NO CONNECTION
 11. ANODE/CATHODE
 12. ANODE/CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 2:
 CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
 2. ANODE
 3. ANODE
 4. NO CONNECTION
 5. ANODE
 6. NO CONNECTION
 7. ANODE
 8. ANODE
 9. ANODE
 10. NO CONNECTION
 11. ANODE
 12. ANODE
 13. NO CONNECTION
 14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
 2. CATHODE
 3. CATHODE
 4. NO CONNECTION
 5. CATHODE
 6. NO CONNECTION
 7. CATHODE
 8. CATHODE
 9. CATHODE
 10. NO CONNECTION
 11. CATHODE
 12. CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. ANODE/CATHODE
 5. ANODE/CATHODE
 6. NO CONNECTION
 7. COMMON ANODE
 8. COMMON CATHODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. ANODE/CATHODE
 12. ANODE/CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
 2. CATHODE
 3. CATHODE
 4. CATHODE
 5. CATHODE
 6. CATHODE
 7. CATHODE
 8. ANODE
 9. ANODE
 10. ANODE
 11. ANODE
 12. ANODE
 13. ANODE
 14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
 2. COMMON ANODE
 3. COMMON CATHODE
 4. ANODE/CATHODE
 5. ANODE/CATHODE
 6. ANODE/CATHODE
 7. ANODE/CATHODE
 8. ANODE/CATHODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. COMMON CATHODE
 12. COMMON ANODE
 13. ANODE/CATHODE
 14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. NO CONNECTION
 5. ANODE/CATHODE
 6. ANODE/CATHODE
 7. COMMON ANODE
 8. COMMON ANODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. NO CONNECTION
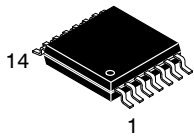 12. ANODE/CATHODE
 13. ANODE/CATHODE
 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC−14 NB		**PAGE 2 OF 2**

TSSOP−14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016

14

SCALE 2:1

1

14X **K** REF

⊕ | 0.10 (0.004) Ⓜ | T | U Ⓢ | V Ⓢ

⬠ 0.15 (0.006) | T | U Ⓢ

2X **L/2**

L

PIN 1
IDENT.

14 8

1 7

B
−U−

A
−V−

⬠ 0.15 (0.006) | T | U Ⓢ

N

0.25 (0.010)

M

N

F

DETAIL E

K

K1

J **J1**

SECTION N−N

C

⬠ 0.10 (0.004)
−T− SEATING
PLANE

D **G** **H**

DETAIL E

−W−
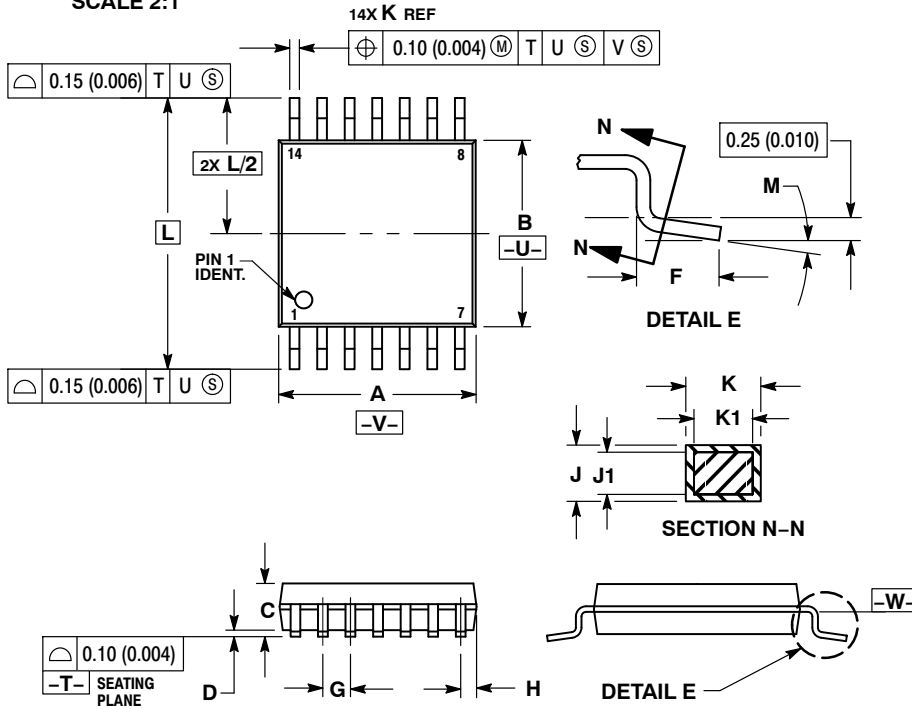
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

|	MILLIMETERS		INCHES	
DIM	**MIN**	**MAX**	**MIN**	**MAX**
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

**GENERIC
MARKING DIAGRAM***

14

XXXX
XXXX
ALYW▪

1
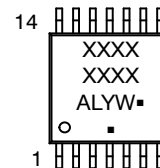
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present.

SOLDERING FOOTPRINT

7.06

1

0.65
PITCH

14X
0.36

14X
1.26

DIMENSIONS: MILLIMETERS
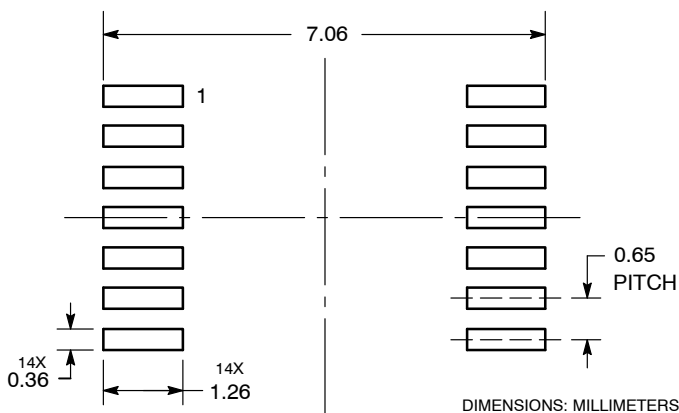
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DESCRIPTION:	TSSOP−14 WB		**PAGE 1 OF 1**